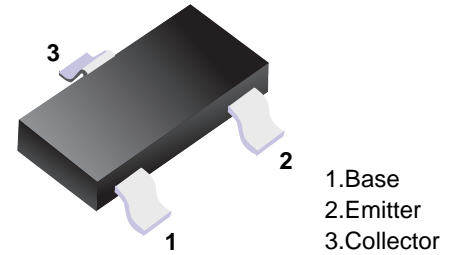


■ PNP Transistors

■ Features

- Collector Current: $I_c = -1.5A$



■ Simplified outline(SOT-23)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_c	-1.5	A
Collector Power Dissipation	P_c	0.3	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

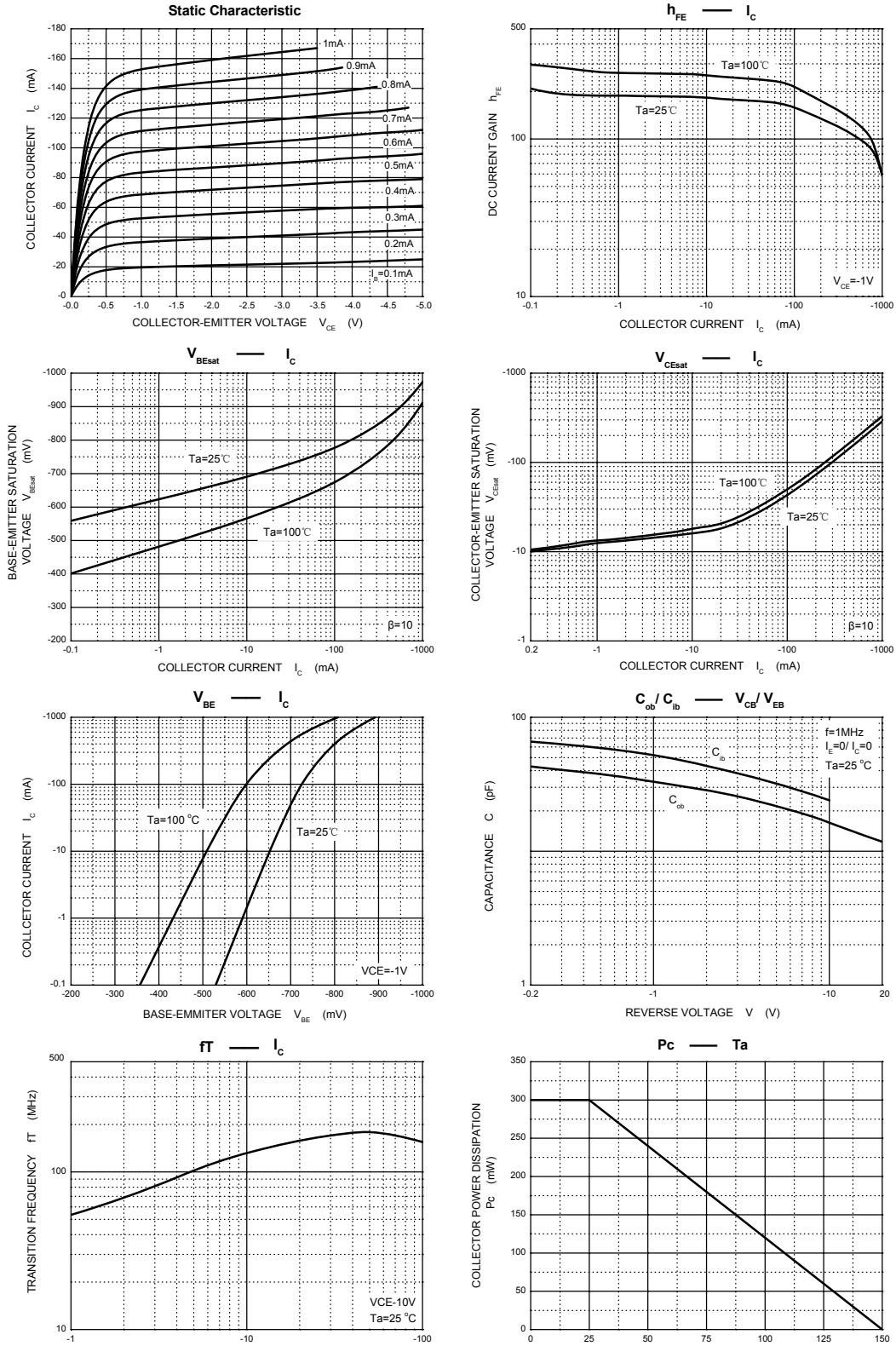
■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_c = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_c = -100mA$	120		400	
		$V_{CE} = -1V, I_c = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -800mA, I_B = -80mA$			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_c = -1V, V_{CE} = -10mA$			-1	V
output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Transition frequency	f_T	$V_{CE} = -10V, I_c = -50mA, f = 30MHz$	100			MHz

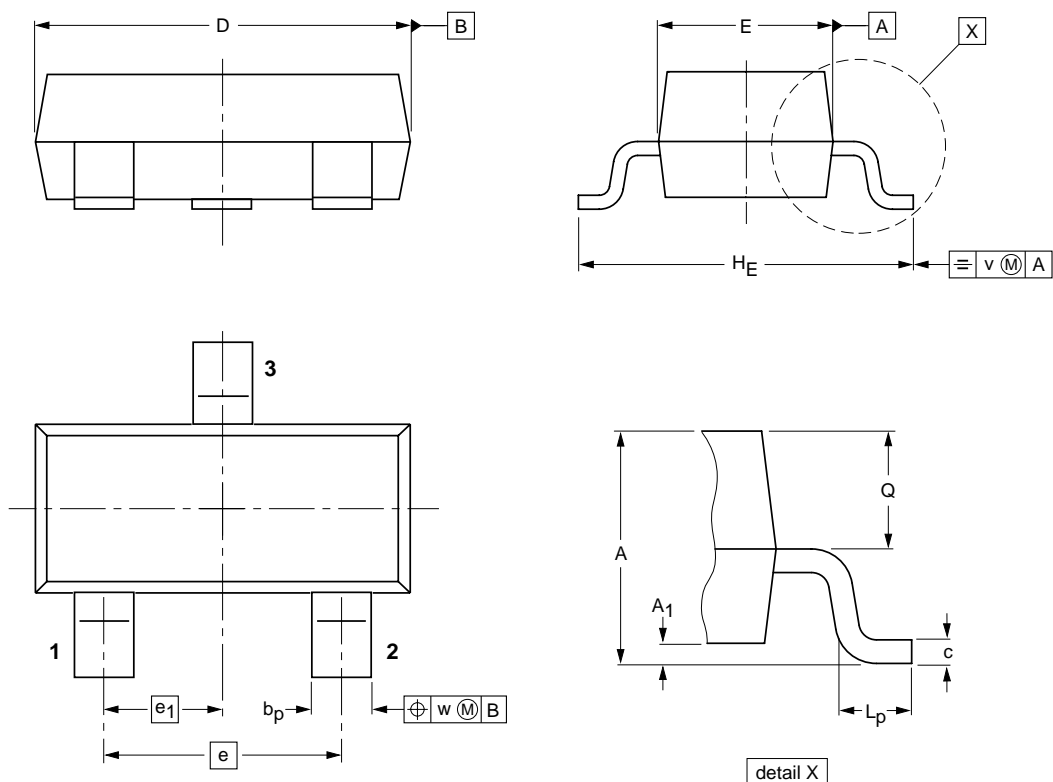
■ $h_{FE}(1)$ Classification

Type	SS8550	SS8550-L	SS8550-H	SS8550-J
Range	200-350	120-200	144-202	300-400
Marking	Y2			

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1